

2SK3047

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed: EAS > 15 mJ
- Gate-source surrender voltage V_{GSS} : ± 30 V guaranteed
- High-speed switching
- No secondary breakdown

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

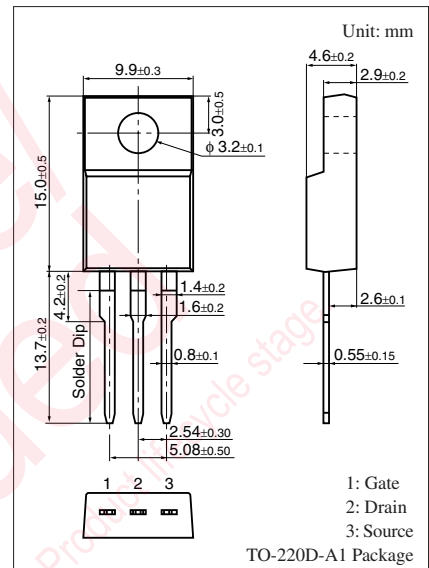
Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	800	V
Gate-source surrender voltage	V_{GSS}	± 30	V
Drain current	I_D	± 2	A
Peak drain current	I_{DP}	± 4	A
Avalanche energy capability *	EAS	15	mJ
Power dissipation	P_D	30	W
		$T_a = 25^\circ\text{C}$	2
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: $L = 7.5$ mH, $I_L = 2$ A, 1 pulse

■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

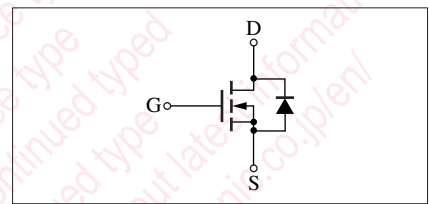
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 1$ mA, $V_{GS} = 0$	800			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 640$ V, $V_{GS} = 0$			100	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 30$ V, $V_{DS} = 0$			± 1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 25$ V, $I_D = 1$ mA	2.0		5.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 25$ V, $I_D = 1$ A	0.7	1.1		S
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 1$ A		4.8	7.0	Ω
Diode forward voltage	V_{DF}	$I_{DR} = 2$ A, $V_{GS} = 0$			-1.3	V
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = 20$ V, $V_{GS} = 0$, $f = 1$ MHz		350		pF
Short-circuit output capacitance (Common source)	C_{oss}			60		pF
Reverse transfer capacitance (Common source)	C_{rss}			25		pF
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 200$ V, $I_D = 1$ A, $R_L = 200$ Ω		15		ns
Rise time	t_r	$V_{GS} = 10$ V		20		ns
Fall time	t_f			25		ns
Turn-off delay time	$t_{d(off)}$			60		ns
Thermal resistance (ch-c)	$R_{th(ch-c)}$				4.1	$^\circ\text{C/W}$
Thermal resistance (ch-a)	$R_{th(ch-a)}$				62.5	$^\circ\text{C/W}$

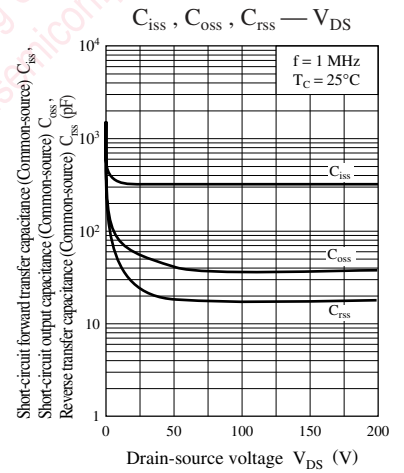
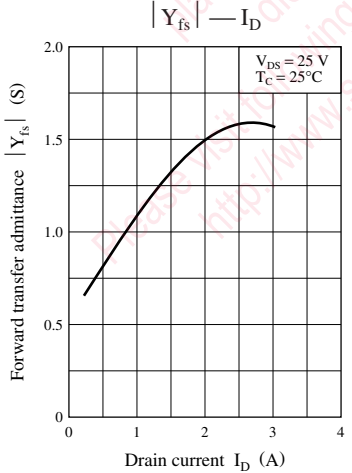
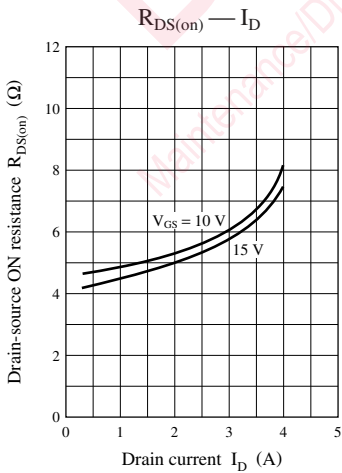
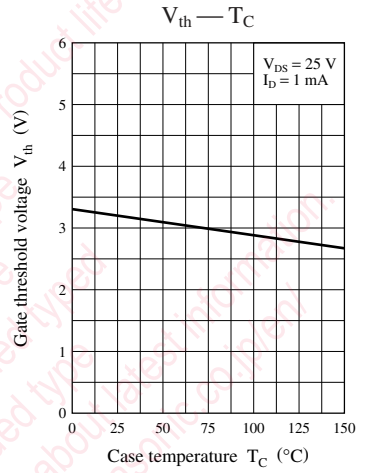
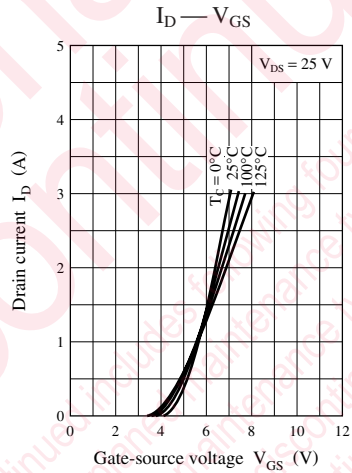
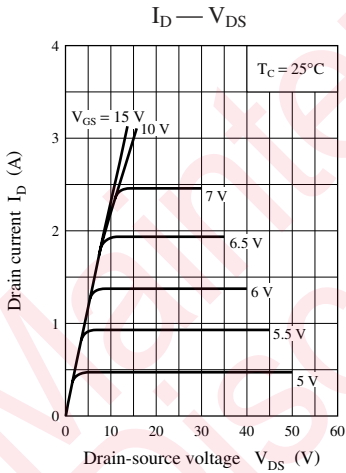
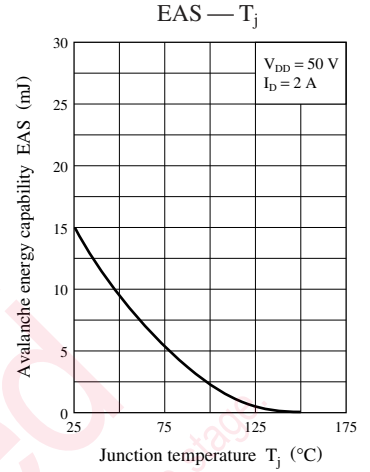
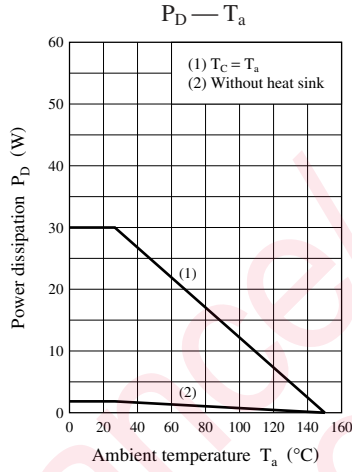
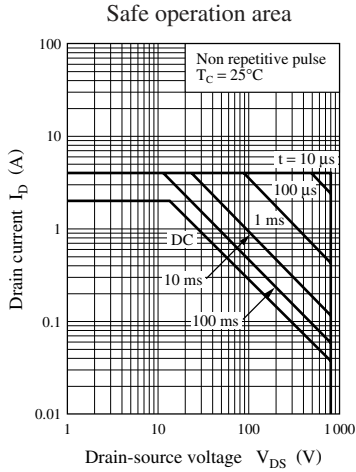
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

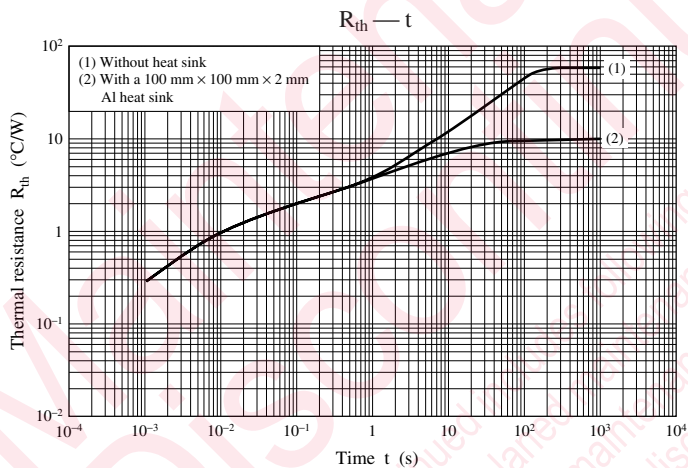
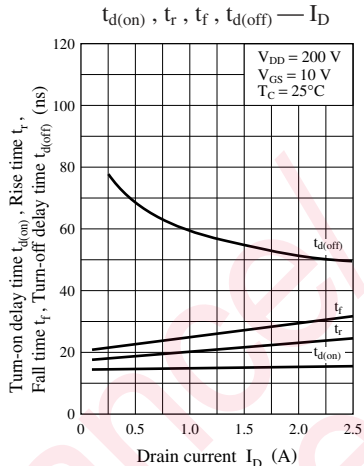
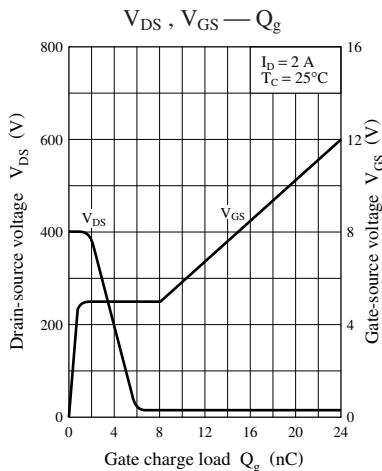


Marking Symbol: K3047

Internal Connection







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